PBSS4041NX 60 V, 6.2 A NPN low VCEsat (BISS) transistor

11 December 2012

Product data sheet

1. Technical summary

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4041PX.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quie	Table 1. Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current			-	-	6.2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	15	А
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C		-	25	35	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3-
3	В	base	3 2 1 SOT89	1 sym042

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS4041NX	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89		

7. Marking

Table 4. Marking codes			
Type number	Marking code		
	[1]		
PBSS4041NX	%6F		

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	6.2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	15	А
I _B	base current			-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	600	mW
			[2]	-	1650	mW
			[3]	-	2500	mW
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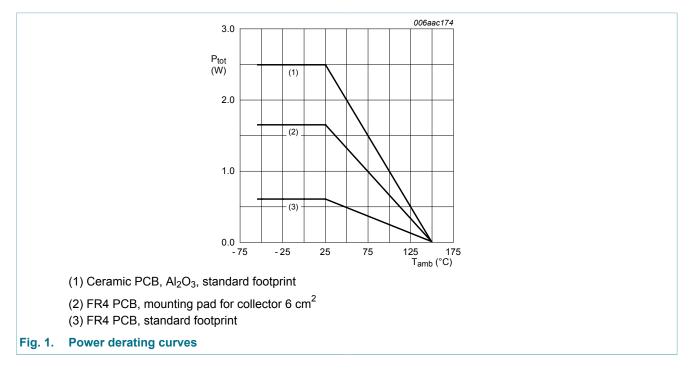
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Symbol	Parameter	Conditions	Min	Мах	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.



9. Thermal characteristics

Table 6. The	Table 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
from junction	thermal resistance	in free air	[1]	-	-	210	K/W
	from junction to ambient		[2]	-	-	75	K/W
	ampient		[3]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

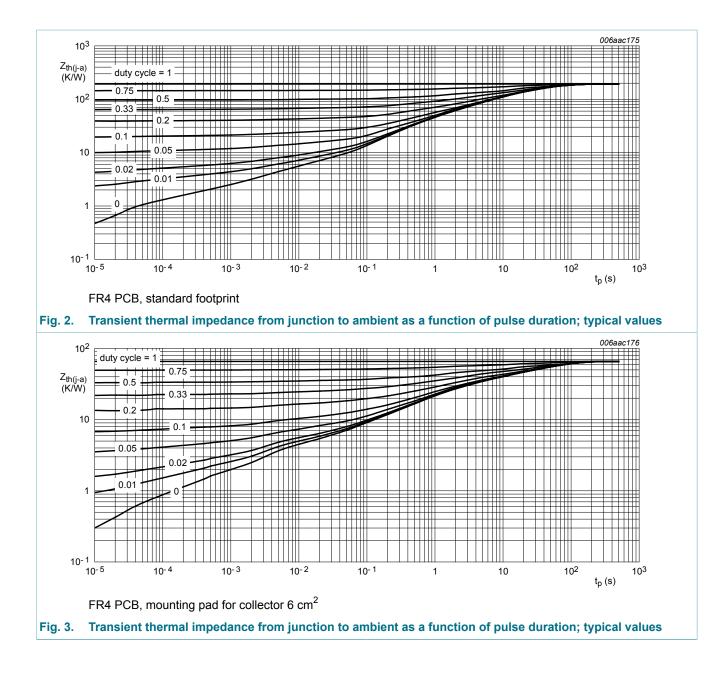
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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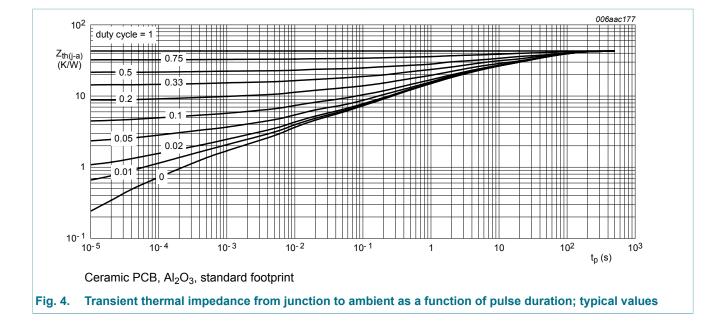
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	$\begin{split} &V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 500 mA; pulsed;} \\ &t_{p} \texttt{\leq 300 } \mu\texttt{s}\texttt{; } \delta \texttt{\leq 0.02 ; } T_{amb} \texttt{= 25 °C} \end{split}$	300	500	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu s; \\ \delta &\leq 0.02 \; ; \; T_{amb} = 25 \; ^\circ C \end{split}$	300	500	-	
		V_{CE} = 2 V; I _C = 2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	250	450	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 4 \text{ A}; \text{ pulsed}; \text{t}_{p} \leq 300 \mu\text{s};$ $\delta \leq 0.02 \text{ ; } \text{T}_{amb} = 25 ^{\circ}\text{C}$	150	250	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 6 A; pulsed; } t_{p} \texttt{\leq 300 } \mu \texttt{s}; \\ \delta \texttt{\leq 0.02 ; } T_{amb} \texttt{= 25 °C} \end{array}$	75	120	-	
V _{CEsat}	collector-emitter saturation voltage	$\begin{split} I_{C} &= 1 \text{ A}; I_{B} = 50 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	35	50	mV
		I_{C} = 1 A; I_{B} = 10 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	50	80	mV

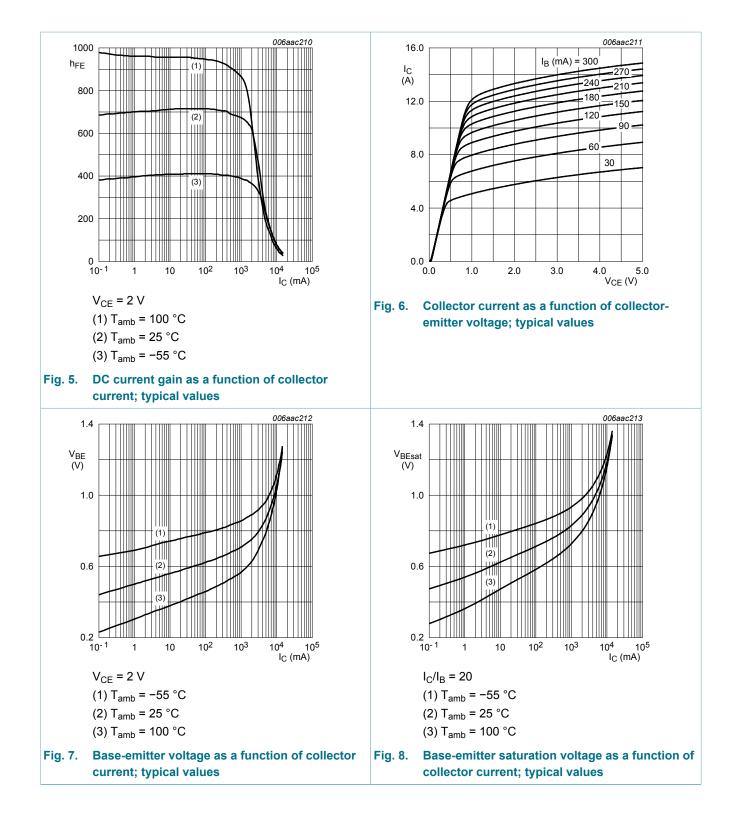
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Symbol	Parameter	Conditions	M	in Typ	Мах	Unit
		I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	95	145	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	110	150	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	240	320	mV
		I_C = 6 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	150	210	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	25	35	mΩ
BEGG	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.82	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.92	1.05	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \; V; \; I_{C} = 2 \; A; \; pulsed; \; t_{p} \leq 300 \; \mu s; \\ \bar{D} \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ} C \end{array}$	-	0.75	0.85	V
t _d	delay time	V_{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	35	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	65	-	ns
t _{on}	turn-on time		-	100	-	ns
ts	storage time		-	1050	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	1270	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	35	-	pF

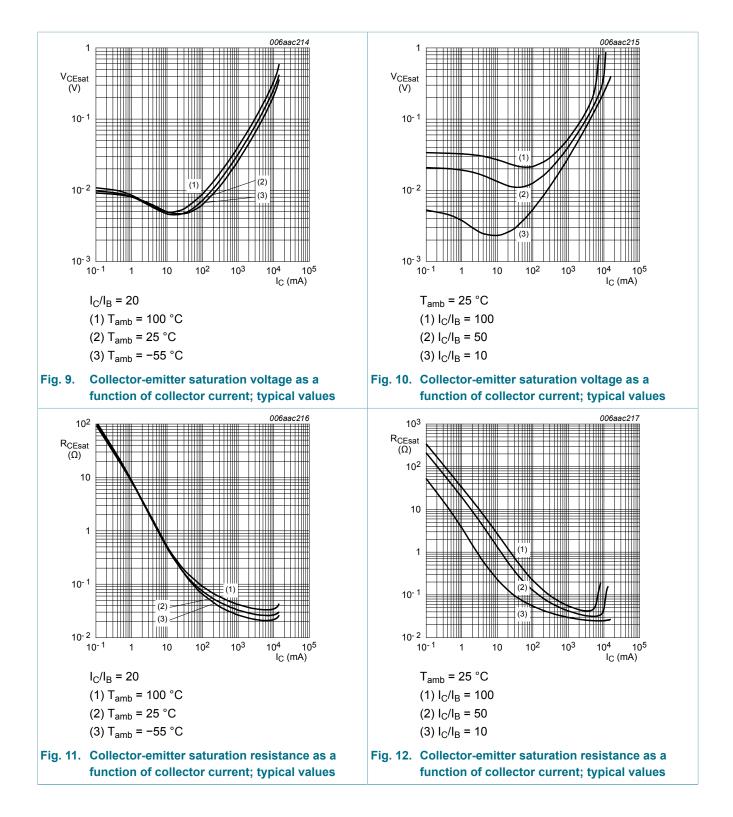
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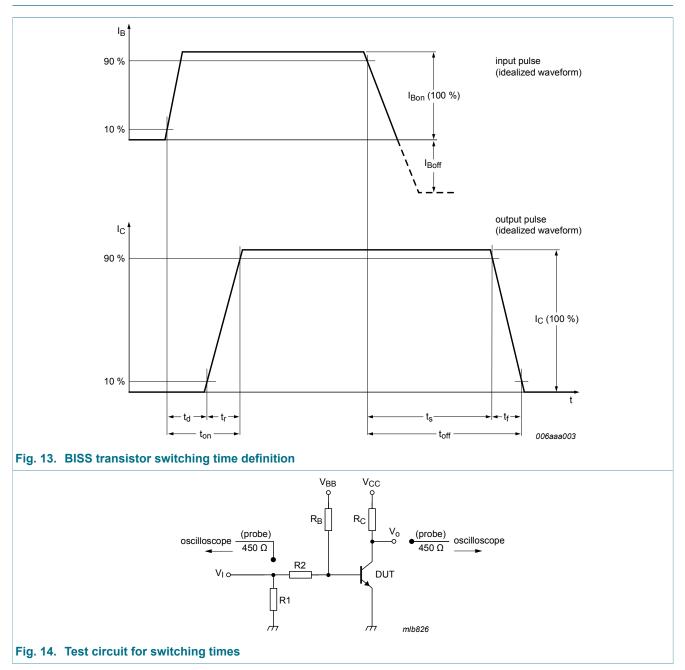
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11. Test information

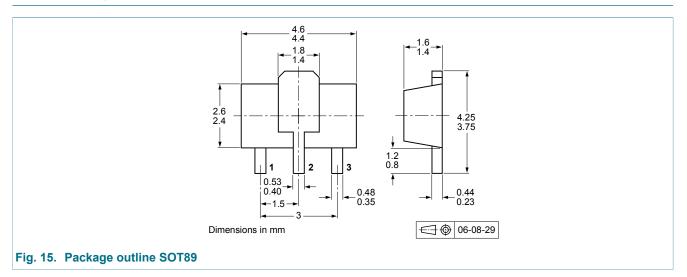
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

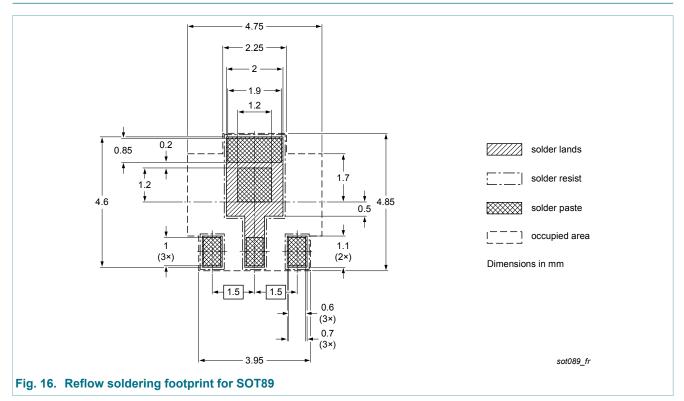
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12. Package outline

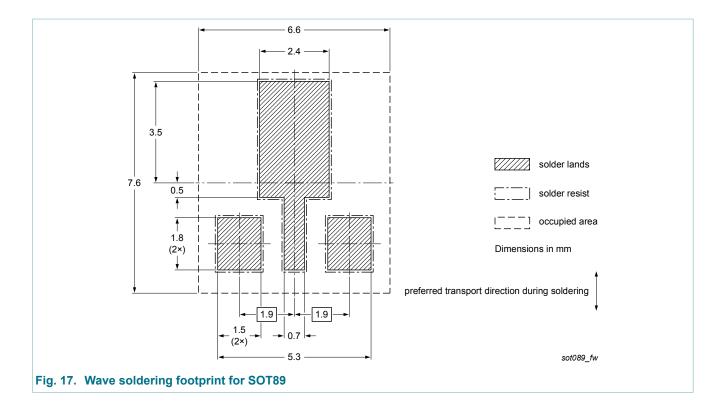


13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4041NX v.3	20121211	Product data sheet	-	PBSS4041NX v.2	
Modifications:	Editorial update	Editorial update			
PBSS4041NX v.2	20121010	Product data sheet	-	PBSS4041NX v.1	
PBSS4041NX v.1	20100401	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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